PATENT ABSTRACTS OF JAPAN

(11)Publication number:

06-118656

(43) Date of publication of application: 28.04.1994

(51)Int.CI.

G03F 7/11 H01L 21/027

(21)Application number: 04-288131

(71)Applicant: JAPAN SYNTHETIC RUBBER CO

LTD

(22)Date of filing:

05.10.1992

(72)Inventor: NEMOTO HIROAKI

ENDO MASAYUKI

ISAMOTO YOSHITSUGU

MIURA TAKAO

(54) REFLECTION PREVENTING FILM AND RESIST PATTERN FORMING METHOD

(57)Abstract:

PURPOSE: To enhance antihalation effect, to prevent sublimation of a radiation absorbing material in a reflection preventing film and occurrence of intermixing, and to obtain superior heat resistance by incorporating a copolymer having at least each one kind of specified repeating unit.

CONSTITUTION: The reflection preventing film contains at least one kind of repeating unit represented by formulae I-III in which each of R1-R3 is, independently, H or an organic group and R1>R2 in formula II; R4 is an organic group having an epoxy group; X is a divalent group; each of R5 and R6 is, independently, H, OH, halogen, or amino; each of R7 and R8 is, independently. an organic group; and each of n and m is an integer.

LEGAL STATUS

[Date of request for examination]

16.10.1998

[Date of sending the examiner's decision of

rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

3082473

[Date of registration]

30.06.2000

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office

* NOTICES *

Japan Patent Office is not responsible for any damages caused by the use of this translation.

- 1. This document has been translated by computer. So the translation may not reflect the original precisely.
- 2.**** shows the word which can not be translated.
- 3.In the drawings, any words are not translated.

CLAIMS

[Claim(s)]

[Claim 1] An antireflection film characterized by containing a copolymer which has one or more sorts of repeating units expressed with a repeating unit expressed with the following type (1), a repeating unit expressed with the following type (2), and the following type (3), respectively.

In [type (1), R1, R2, and R3 may be mutually the same, or they may differ from each other, and show a hydrogen atom or an organic radical.]

[Formula 2]
$$\begin{array}{c|c}
R^1 & R^3 \\
 \hline
\begin{pmatrix}
c & -c \\
-c & -c
\end{pmatrix}$$

$$\begin{array}{c|c}
R^2 & R^4
\end{array}$$
... (2)

In [type (2), R1, R2, and R3 may be mutually the same, or you may differ, a hydrogen atom or an organic radical is shown, and R4 shows an epoxy group content organic radical.]

[Formula 3]
$$\begin{array}{c|cccc}
R^1 & R^3 \\
\hline
\begin{pmatrix} c & -c \\
 & c \\
 & c \\
 & R^2 & X
\end{array}$$

$$\begin{array}{c|cccc}
 & R^7 \\
 & C \\
 & C \\
 & R^8 \\
 & R^6 \\
 & R^6$$

In [type (3), R1, R2, and R3 may be mutually the same, or they may differ. A hydrogen atom or an organic radical is shown and it is X. A divalent radical or single bond is shown. R5 and R6 may be mutually the same, or they may differ. A hydrogen atom, a halogen atom, a hydroxyl group, the amino group, a nitro group, or an organic radical is shown, R7 and R8 may be mutually the same, or you may differ, a hydrogen atom, a halogen atom, the amino group, or an organic radical is shown, n is the integer of 1-4, and m is the integer of 1-5.]

[Claim 2] A formation method of a resist pattern which in forming a resist pattern by applying a resist,

| forming a resist film on a substrate, irradiating radiation on this resist film at a predetermined pattern |
|--|
| configuration, and subsequently developing negatives is beforehand characterized by forming a resist |
| film after forming an antireflection film according to claim 1 on a substrate. |

[Translation done.]